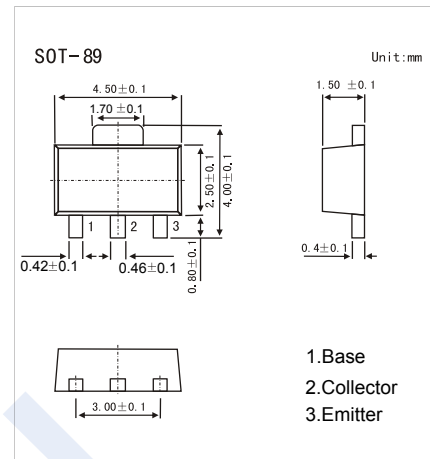


PNP Transistors

2SB1026-HF

■ Features

- Low frequency power amplifier
- Complementary to 2SD1419-HF
- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CBO}	-120	V
Collector - Emitter Voltage	V _{CEO}	-100	
Emitter - Base Voltage	V _{EBO}	-5	
Collector Current - Continuous	I _C	-1	A
Collector current -Pulse (Note.1)	I _{CP}	-2	
Collector Power Dissipation	P _C	1	W
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

Note.1: PW ≤ 10ms, Duty cycle ≤ 20%

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CBO}	I _C = -100 μA, I _E = 0	-120			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -1 mA, R _{BE} = ∞	-100			
Emitter - base breakdown voltage	V _{EBO}	I _E = -100 μA, I _C = 0	-5			
Collector-base cut-off current	I _{CBO}	V _{CB} = -100V, I _E = 0			-10	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C = 0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -500mA, I _B = -50mA			-1	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C = -500mA, I _B = -50mA			-1.2	
Base - emitter voltage	V _{BE}	V _{CE} = -5V, I _C = -150 mA			-0.9	
DC current gain	h _{FE}	V _{CE} = -5V, I _C = -150 mA	60		200	
		V _{CE} = -5V, I _C = -500 mA	30			
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz		20		pF
Transition frequency	f _T	V _{CE} = -5V, I _C = -150mA		140		MHz

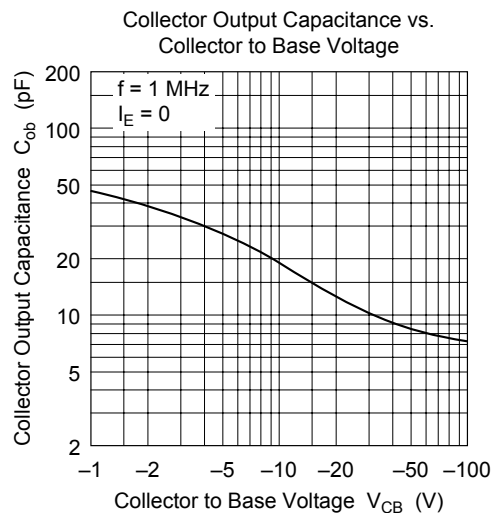
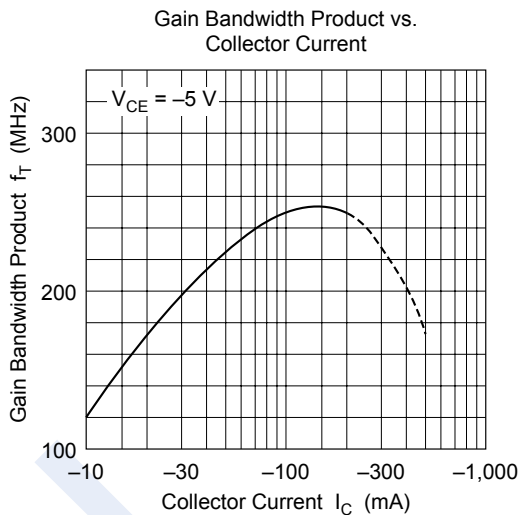
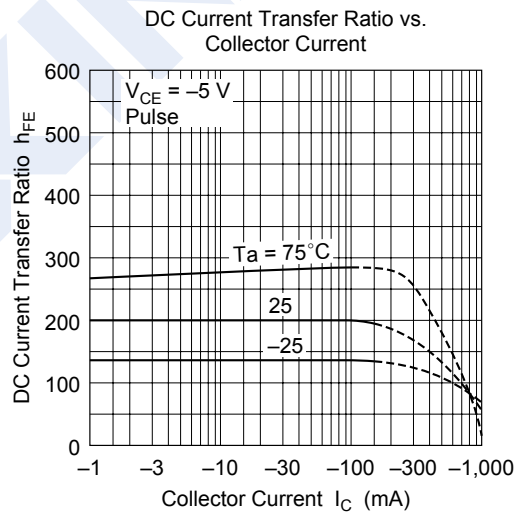
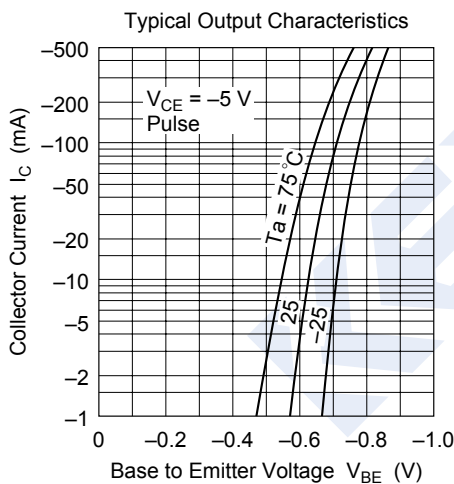
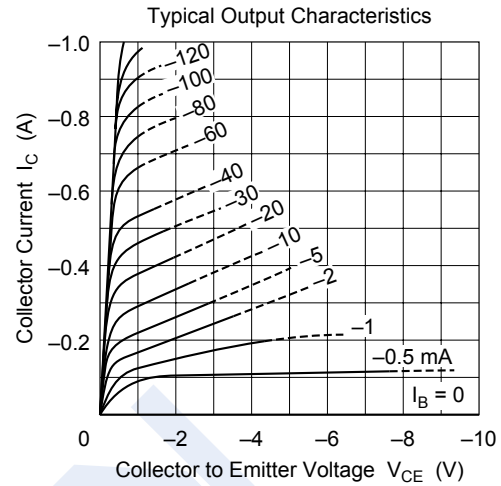
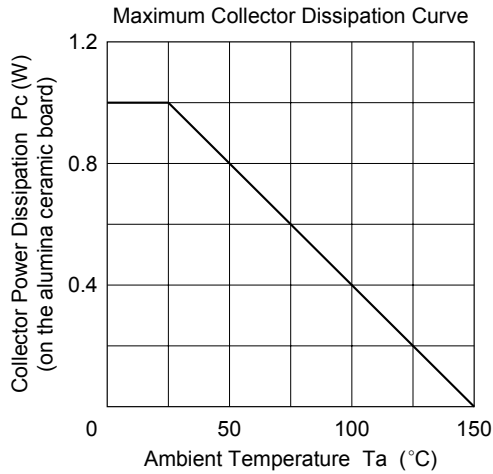
■ Classification of h_{FE}(1)

Type	2SB1026-L-HF	2SB1026-M-HF
Range	60-120	100-200
Marking	DL _F	DM _F

PNP Transistors

2SB1026-HF

■ Typical Characteristics



PNP Transistors

2SB1026-HF

■ Typical Characteristics

